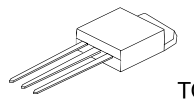
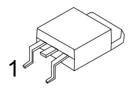
9 N03

Power MOSFET

9Amps, 30 Volts
N-CHANNEL POWER MOSFET





*Pb-free plating product number: YR09N03

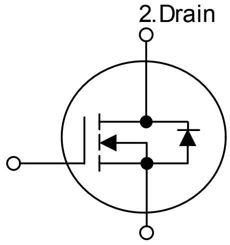
■ DESCRIPTION

The YR 09N03 is a low voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and excellent avalanche characteristics. This power MOSFET is usually used at automotive applications in power supplies, high efficient DC to DC converters and battery operated products.

■ FEATURES

* $R_{DS(ON)}$ = 28mΩ@V_{GS} = 10 V
* Ultra low gate charge (typical 7 nC)
* Low reverse transfer Capacitance (C_{RSS} = typical 70 pF)
* Fast switching capability
* 100% avalanche energy specified
* Improved dv/dt capability

■ SYMBOL



■ ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current	T_A=25℃	I_D	9.0	A
	T_A=70℃		7.6	
Pulsed Drain Current [C]		I_{DM}	35	
Power Dissipation [B]	T_A=25℃	P_D	1.6	W
	T_A=70℃		1.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	℃

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	70	90	℃/W
Maximum Junction-to-Ambient [A D]	Steady-State		100	125	℃/W
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	63	80	℃/W

■ ELECTRICAL CHARACTERISTICS (T_C = 25℃, unless otherwise specified)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
STATIC PARAMETERS							
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V		30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V				1	μA
			T_J=55℃			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±12V				100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250μA		0.65	1.05	1.45	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V		30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=5.8A			18	28	mΩ
			T_J=125℃		28	39	
		V_{GS}=4.5V, I_D=5A			19	33	mΩ
		V_{GS}=2.5V, I_D=4A			24	52	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=5.8A			33		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V			0.7	1	V
I_S	Maximum Body-Diode Continuous Current					2	A
DYNAMIC PARAMETERS							
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		500	630	760	pF
C_{oss}	Output Capacitance			50	75	100	pF
C_{rss}	Reverse Transfer Capacitance			30	50	70	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		1.5	3	4.5	Ω
SWITCHING PARAMETERS							
Q_g	Total Gate Charge	V_{GS}=4.5V, V_{DS}=15V, I_D=5.8A		4.8	6	7	nC
Q_{gs}	Gate Source Charge			1	1.3	1.6	nC
Q_{gd}	Gate Drain Charge			1	1.8	2.5	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=2.6Ω, R_{GEN}=3Ω			3		ns
t_r	Turn-On Rise Time				2.5		ns
$t_{D(off)}$	Turn-Off DelayTime				25		ns
t_f	Turn-Off Fall Time				4		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=5.8A, dI/dt=100A/μs		7	8.5	10	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=5.8A, dI/dt=100A/μs		2	2.6	3.1	nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using ≤ 10s junction-to-ambient thermal resistance.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C. Ratings are based on low frequency and duty cycles to keep initialT_J=25° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

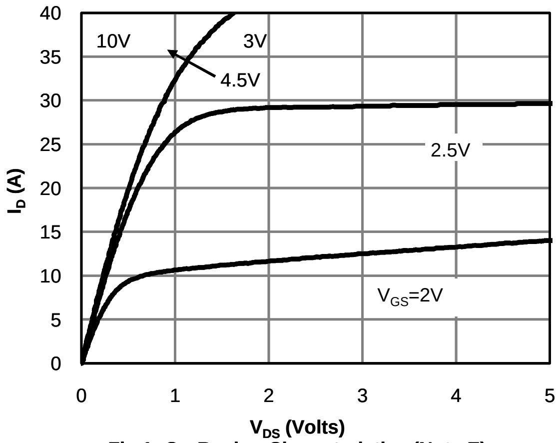


Fig 1: On-Region Characteristics (Note E)

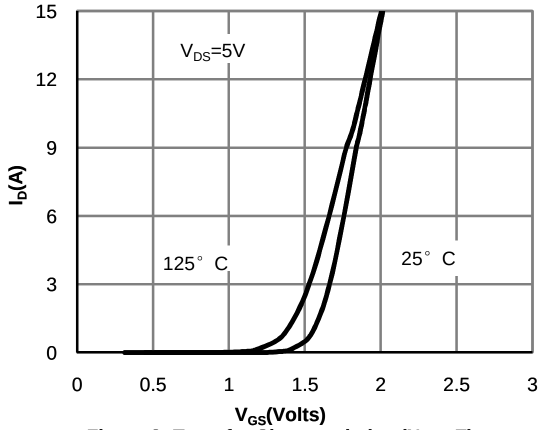


Figure 2: Transfer Characteristics (Note E)

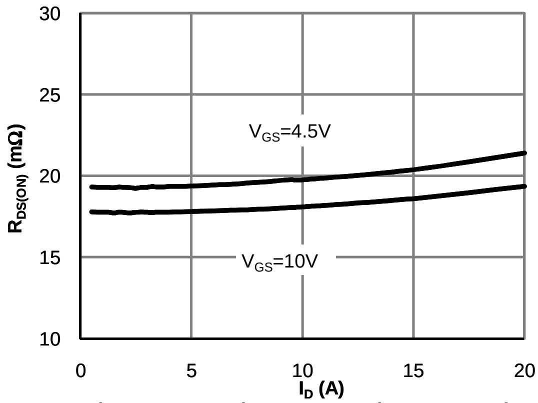


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

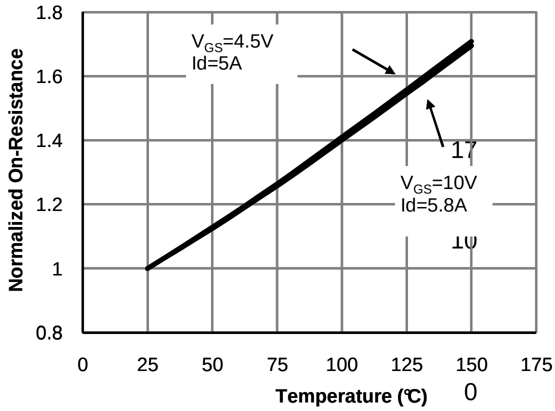


Figure 4: On-Resistance vs. Junction Temperature (Note E)

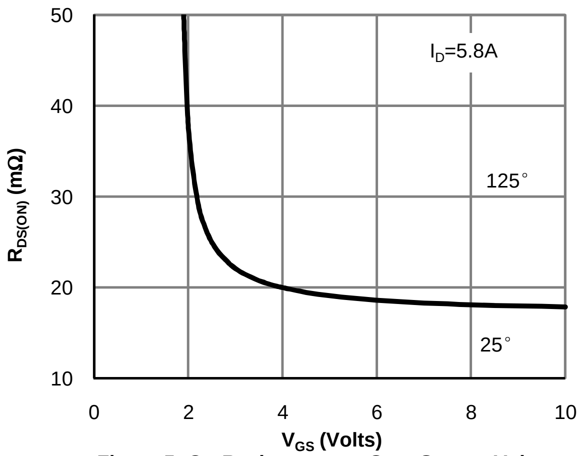


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

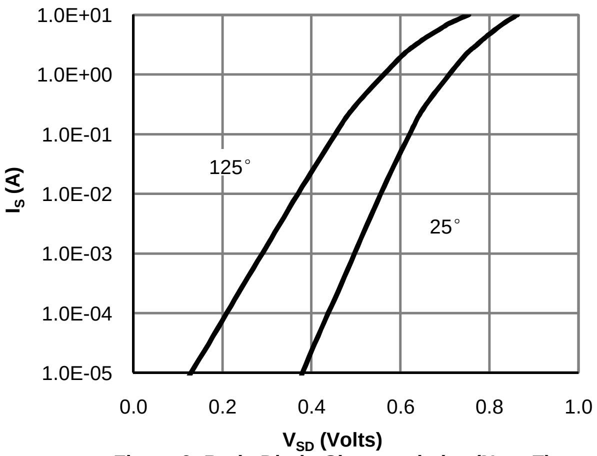


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

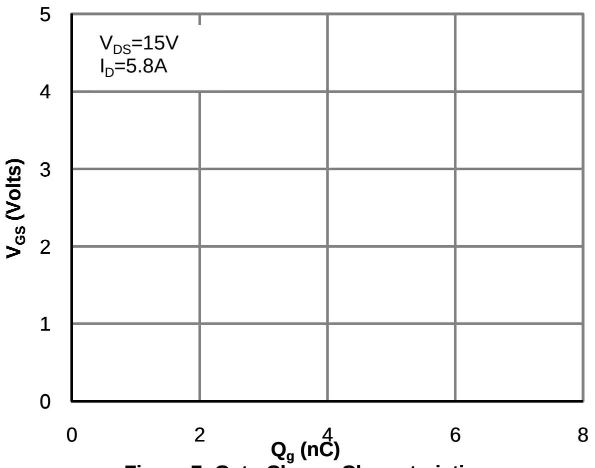


Figure 7: Gate-Charge Characteristics

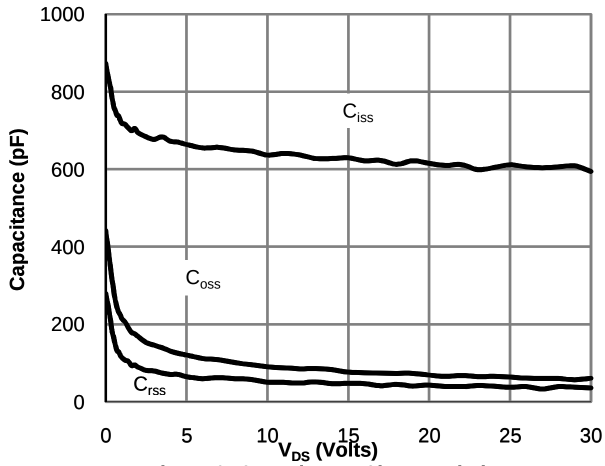


Figure 8: Capacitance Characteristics

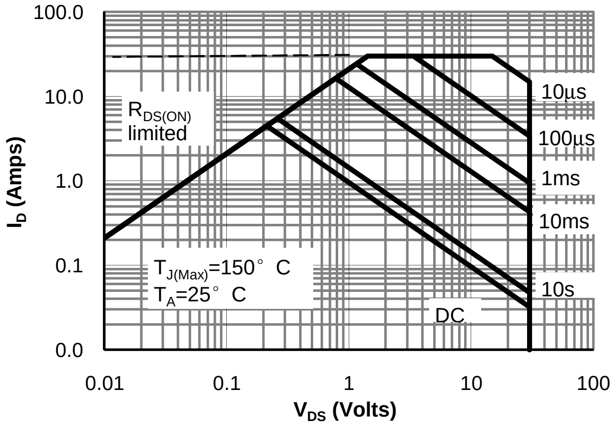


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

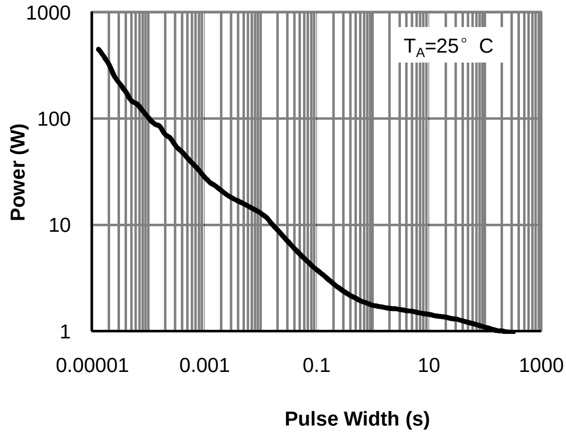


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

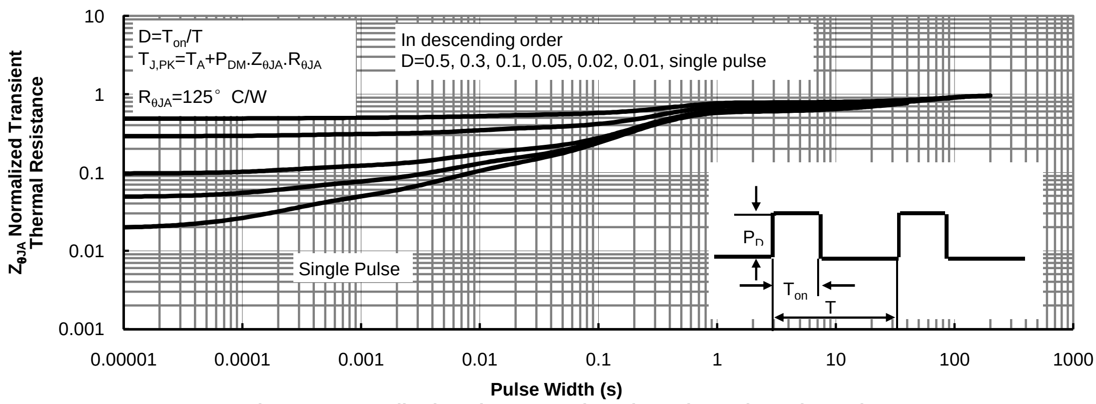
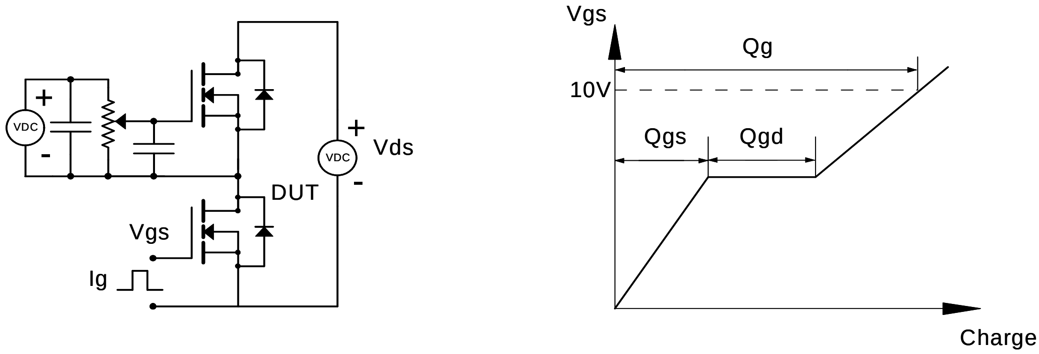
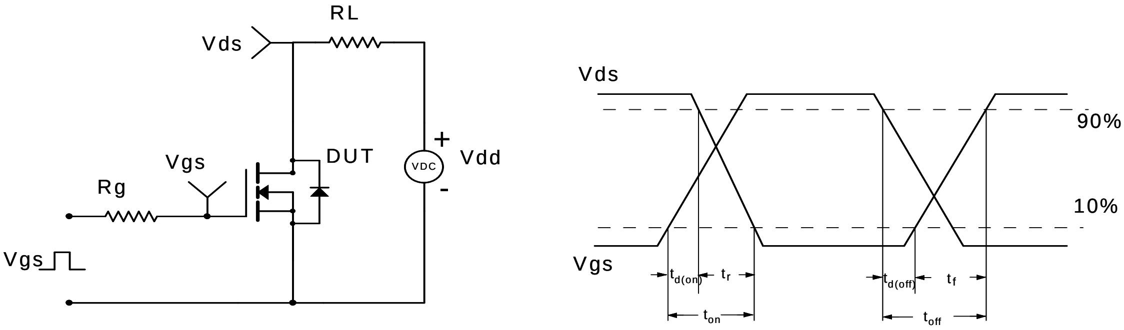


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms